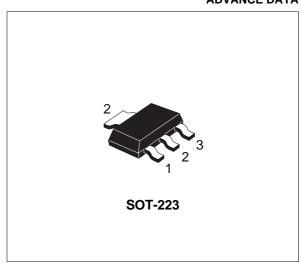


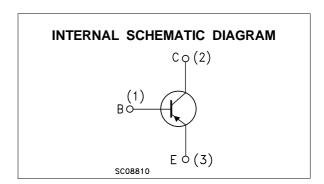
BCP52/53

MEDIUM POWER AMPLIFIER

ADVANCE DATA

- SILICON EPITAXIAL PLANAR PNP TRANSISTORS
- MINIATURE PLASTIC PACKAGE FOR APPLICATION IN SURFACE MOUNTING CIRCUITS
- GENERAL PURPOSE MAINLY INTENDED FOR USE IN MEDIUM POWER INDUSTRIAL APPLICATION AND FOR AUDIO AMPLIFIER OUTPUT STAGE
- NPN COMPLEMENTS ARE BCP55 AND BCP56 RESPECTIVELY





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Va	Value		
		BCP52	BCP53		
V _{CBO}	Collector-Base Voltage (I _E = 0)	-60	-100	V	
Vceo	Collector-Emitter Voltage (I _B = 0)	-60	-80	V	
V _{CER}	Collector-Emitter Voltage ($R_{BE} = 1K\Omega$)	-60	-100	V	
V _{EBO}	Emitter-Base Voltage (I _C = 0)	-5		V	
Ic	Collector Current	-1		Α	
I _{CM}	Collector Peak Current (t _p < 5 ms)	-1.5		Α	
I _B	Base Current	-0.1		Α	
I _{BM}	Base Peak Current (t _p < ms)	-0.2		Α	
P _{tot}	Total Dissipation at T _c = 25 °C	2		W	
T _{stg}	Storage Temperature	-65 to 150		°C	
Tj	Max. Operating Junction Temperature	150		°C	

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THERMAL DATA

R _{thj-amb} •	Thermal Resistance Ju	unction-Ambient Max	62.5	°C/W
R _{thj-tab} ●	Thermal Resistance Ju	unction-Collecor Tab Max	8	°C/W

Mounted on a ceramic substrate area = 30 x 35 x 0.7 mm

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

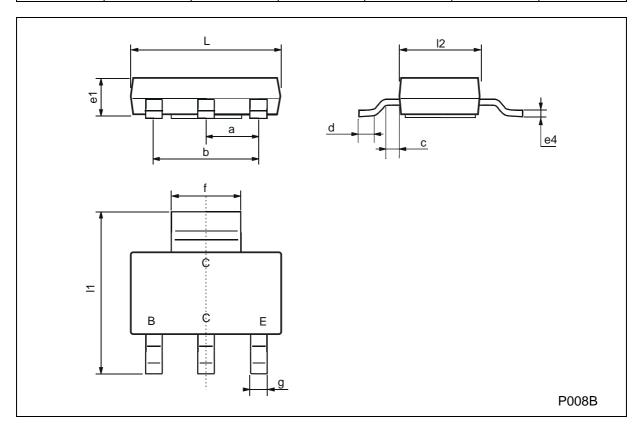
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	$V_{CB} = -30 \text{ V}$ $V_{CB} = -30 \text{ V}$ $T_j = 125 ^{\circ}\text{C}$			-100 -10	nΑ μΑ
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	I _C = -100 μA for BCP52 for BCP53	-60 -100			V V
V _{(BR)CEO*}	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = -20 mA for BCP52 for BCP53	-60 -80			V V
V _(BR) CER	Collector-Emitter Breakdown Voltage (R _{BE} = 1 KΩ)	I _C = -100 μA for BCP52 for BCP53	-60 -100			V V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _C = -10 μA	-5			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = -500 mA I _B = -50 mA			-0.5	V
V _{BE(on)} *	Base-Emitter On Voltage	I _C = -500 mA V _{CE} = -2 V			-1	V
h _{FE} *	DC Current Gain	I _C = -5 mA	25 40 63 100 25		100 160 250	
f _T	Transition Frequency	$I_C = -10 \text{ mA } V_{CE} = -5 \text{ V} f = 35 \text{ MHz}$		50		MHz

^{*} Pulsed: Pulse duration = 300 μs, duty cycle ≤ 1.5 %



SOT-223 MECHANICAL DATA

DIM.	mm			mils			
2	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
а	2.27	2.3	2.33	89.4	90.6	91.7	
b	4.57	4.6	4.63	179.9	181.1	182.3	
С	0.2	0.4	0.6	7.9	15.7	23.6	
d	0.63	0.65	0.67	24.8	25.6	26.4	
e1	1.5	1.6	1.7	59.1	63	66.9	
e4			0.32			12.6	
f	2.9	3	3.1	114.2	118.1	122.1	
g	0.67	0.7	0.73	26.4	27.6	28.7	
I1	6.7	7	7.3	263.8	275.6	287.4	
12	3.5	3.5	3.7	137.8	137.8	145.7	
L	6.3	6.5	6.7	248	255.9	263.8	



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